

ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device comprising
a porous film formed above a semiconductor substrate,
the porous film having at least one burying concave
5 selected from the group consisting of a trench and
a hole, a conductive barrier layer formed on the inner
surface of the burying concave, a conductive member
buried in the burying concave with the conductive
barrier layer interposed between the porous film and
10 the conductive member, and a mixed layer formed between
the porous film and the conductive barrier layer,
and containing a component of the porous film and
a component of the conductive barrier layer.